

## KSP25/26/27

### **Darlington Transistor**

 Collector-Emitter Voltage: V<sub>CES</sub>=KSP25: 40V KSP26: 50V

KSP27: 60V

• Collector Power Dissipation: P<sub>C</sub> (max) =625mW



## **NPN Epitaxial Silicon Darlington Transistor**

## **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage		
	: KSP25	40	V
	: KSP26	50	V
	: KSP27	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current	500	mA
P <sub>C</sub>	Collector Power Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55~150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0			
	: KSP25		40		V
	: KSP26		50		V
	: KSP27		60		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0			
	: KSP25		40		V
	: KSP26		50		V
	: KSP27		60		V
I <sub>CBO</sub>	Collector Cut-off Current				
	: KSP25	$V_{CE}=30V$ , $I_{E}=0$		100	nA
	: KSP26	$V_{CE}=40V$ , $I_{E}=0$		100	nA
	: KSP27	$V_{CE} = 50V, I_{E} = 0$		100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =10V, I <sub>B</sub> =0		100	nA
h <sub>FE</sub>	* DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	10K		
		$V_{CE}=5V$ , $I_{C}=100$ mA	10K		
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> =100mA, I <sub>B</sub> =0.1mA		1.5	V
V <sub>BE</sub> (on)	* Base-Emitter On Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA		2	V

<sup>\*</sup> Pulse Test: PW≤300μs, Duty Cycle≤2%

# **Typical Characteristics**

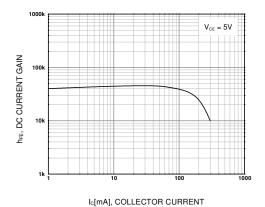


Figure 1. DC current Gain

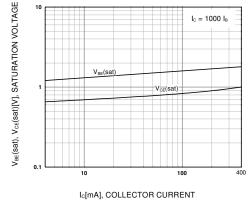


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

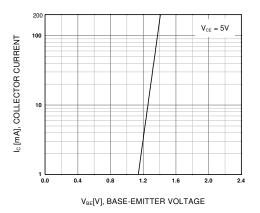


Figure 3. Base-Emitter On Voltage

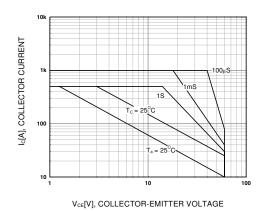
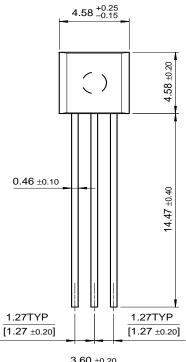
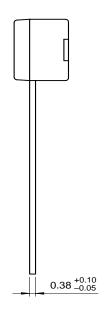


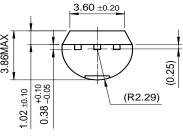
Figure 4. Safe Operating Area

# **Package Dimensions**

TO-92







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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	OCXTM	RapidConfigure™	UHC™
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The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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Rev. I1

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